

QLF093A-05A0/QLF093D-05A0

905 nm 100mW FP LASER TO-CAN

C00112-03 June 2022



1. DESCRIPTION

The QLF093x-05A0 series is a 905 nm quantum well laser device designed for high output power application. The laser diode is mounted into a TO-56 header including a monitor PD and hermetic sealed with a flat glass cap.

2. FEATURES

- 905 nm FP-LD
- $\Phi 5.6\text{mm}$ TO-CAN package
- High output power
- Lateral single mode
- Including monitor PD
- Two types of pin assignments: Anode common type (QLF093A-05A0)/cathode common type (QLF093D-05A0)

3. APPLICATIONS

- Sensing
- Industrial application

4. ABSOLUTE MAXIMUM RATING

(CW operation, $T_c = 25^\circ\text{C}$, unless otherwise specified)

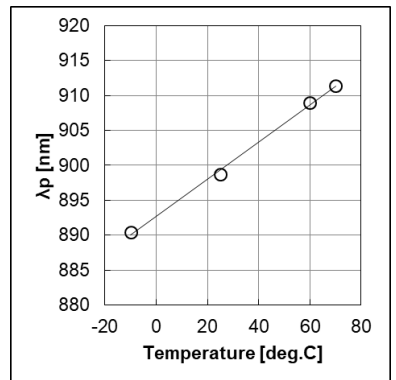
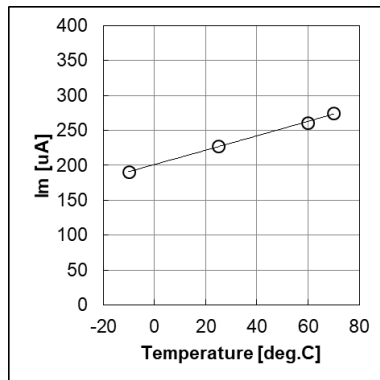
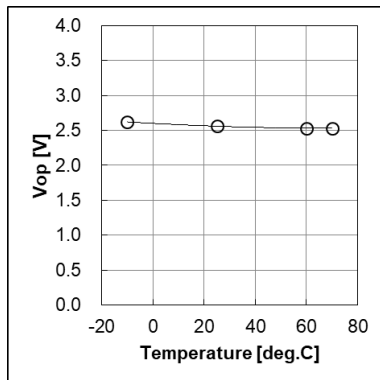
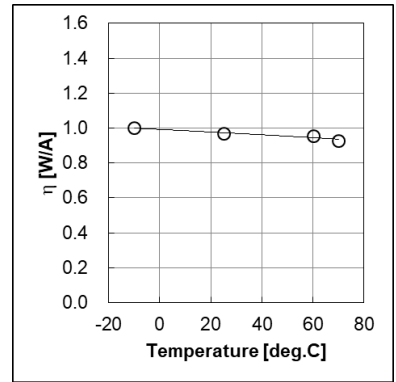
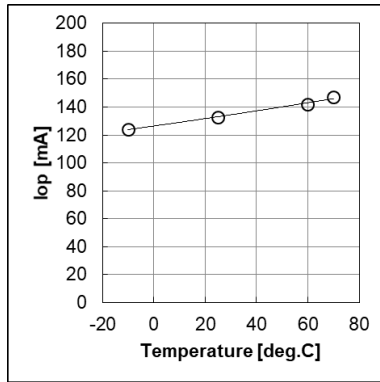
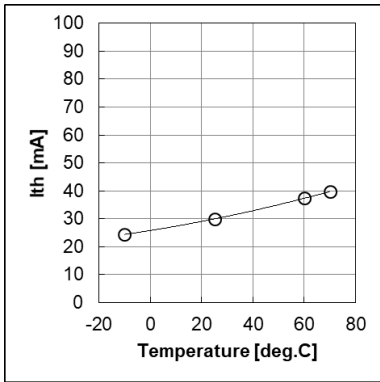
| PARAMETER | SYMBOL | RATING | UNIT |
|-----------------------|-----------------------|-----------|------------------|
| Optical output power | $P_o(\text{CW})$ | 150 | mW |
| | $P_o(\text{Pulse})^*$ | 300 | mW |
| LD reverse voltage | V_{RLD} | 2 | V |
| PD reverse voltage | V_{RPD} | 30 | V |
| Operation temperature | T_c | -10 to 70 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -40 to 85 | $^\circ\text{C}$ |

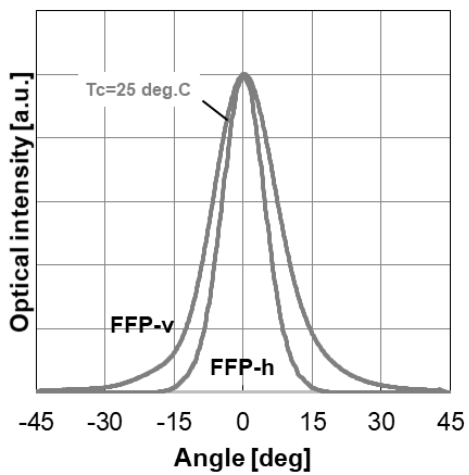
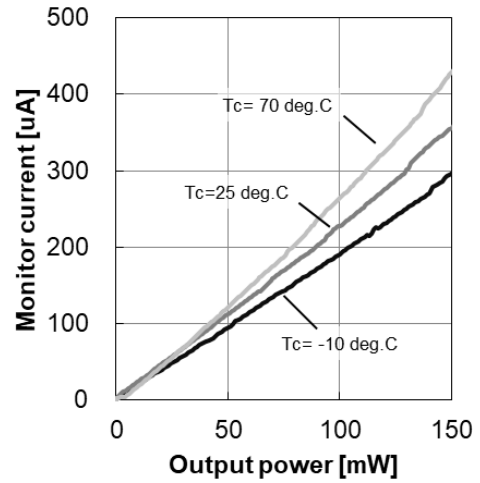
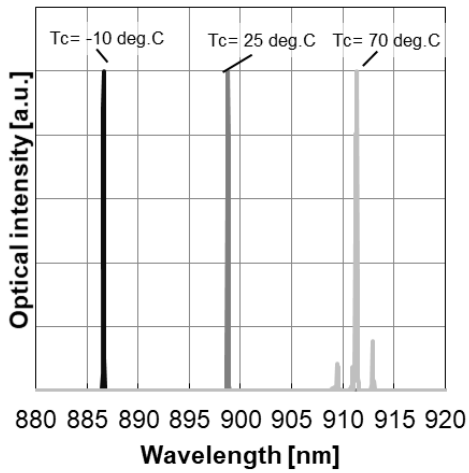
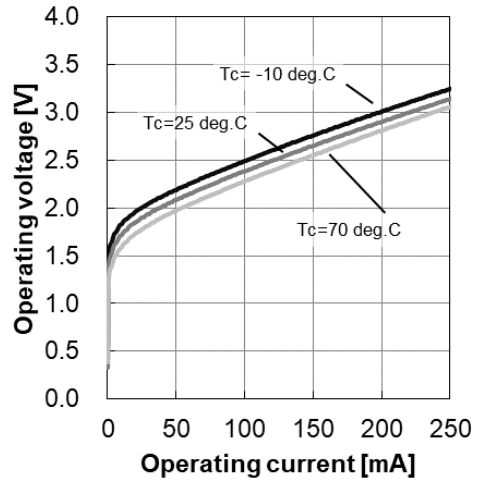
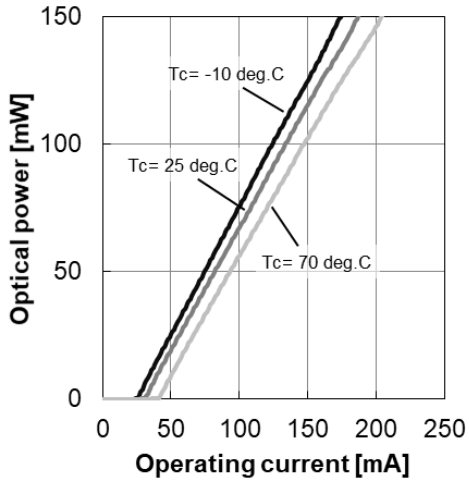
*note : Pulse width < 100nsec, Duty < 50%

5. OPTICAL AND ELECTRICAL CHARACTERISTICS

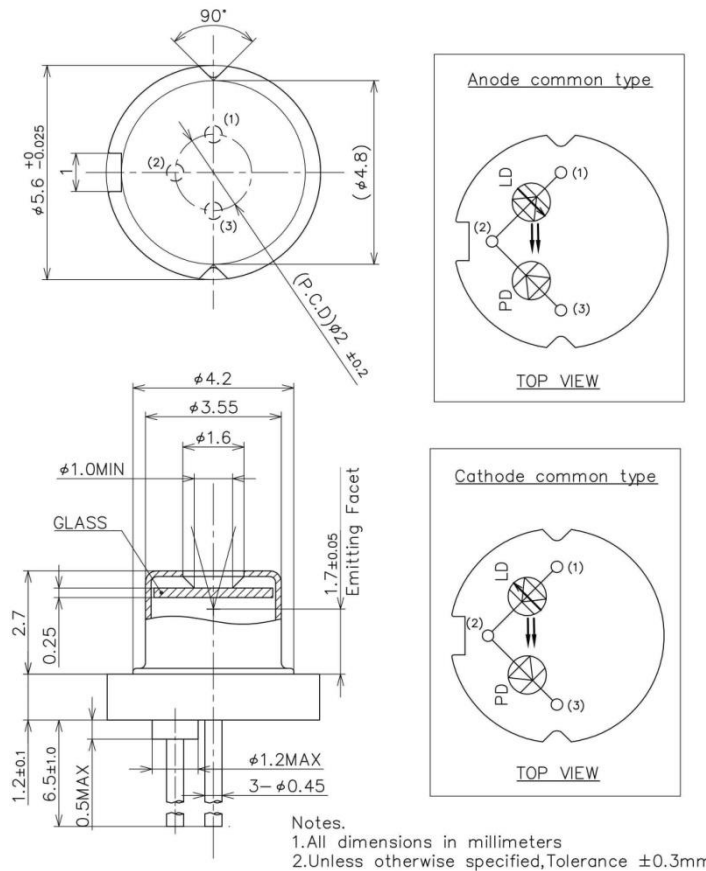
(T_c = 25°C, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITION | MIN | TYP | MAX | UNIT |
|-------------------------------|-----------------|---|-----|-----|-----|------|
| Threshold current | I _{th} | CW | - | 30 | 55 | mA |
| Operation current | I _{op} | CW, P _o =100mW | - | 137 | 160 | mA |
| Operation voltage | V _{op} | CW, P _o =100mW | - | 2.5 | 3.0 | V |
| Slope efficiency | η | CW, P _o =5 - 100mW | 0.8 | 0.9 | - | W/A |
| Monitor current | I _m | CW, P _o =100mW, V _{RD} =5 V | 50 | 350 | 600 | μA |
| Peak wavelength | λ _p | CW, P _o =100mW | 885 | 905 | 915 | nm |
| Far filed pattern, horizontal | θ _h | CW, P _o =100mW | 8 | 11 | 14 | deg. |
| Far filed pattern, vertical | θ _v | CW, P _o =100mW | 14 | 17 | 20 | deg. |
| Tilt angle, horizontal | dθ _h | CW, P _o =100mW | -3 | - | 3 | deg. |
| Tilt angle, vertical | dθ _v | CW, P _o =100mW | -3 | - | 3 | deg. |
| Emitting point accuracy | Δx, Δy, Δz | - | -50 | - | 50 | μm |





6. Outline Drawing



7. Notice

• Safety Information

This product is classified as Class 3B laser product, and complies with 21 CFR Part 1040.10. Please do not take a look at laser lighting in operations since laser devices may cause troubles to human eyes. Please do not eat, burn, break and make chemical process of the products since they contain GaAs material.

• Handling products

Semiconductor lasers are easily damaged by external stress such as excess temperature and ESD. Please pay attention to handling products, and use within range of maximum ratings. QD Laser takes no responsibility for any failure or unusual operation resulting from improper handling, or unusual physical or electrical stress.

• RoHS

This product conforms to RoHS compliance related Directive (EU) 2015/863.

QD Laser, Inc.

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